

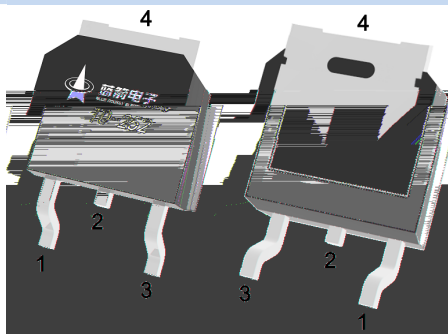
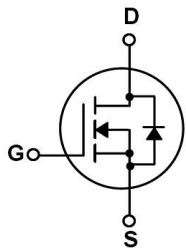
Rev.B Jul.-2023

TO-252 N
 N-CHANNEL MOSFET in a TO-252 Plastic Package.

$R_{DS(on)}$ C_{rss}
 Low $R_{DS(on)}$, low gate charge, low C_{rss} , fast switching, HF Product.

DC/DC

Suited for low voltage applications such as automotive, DC/DC Converters, and high efficiency switching for power management in portable and battery operated products.



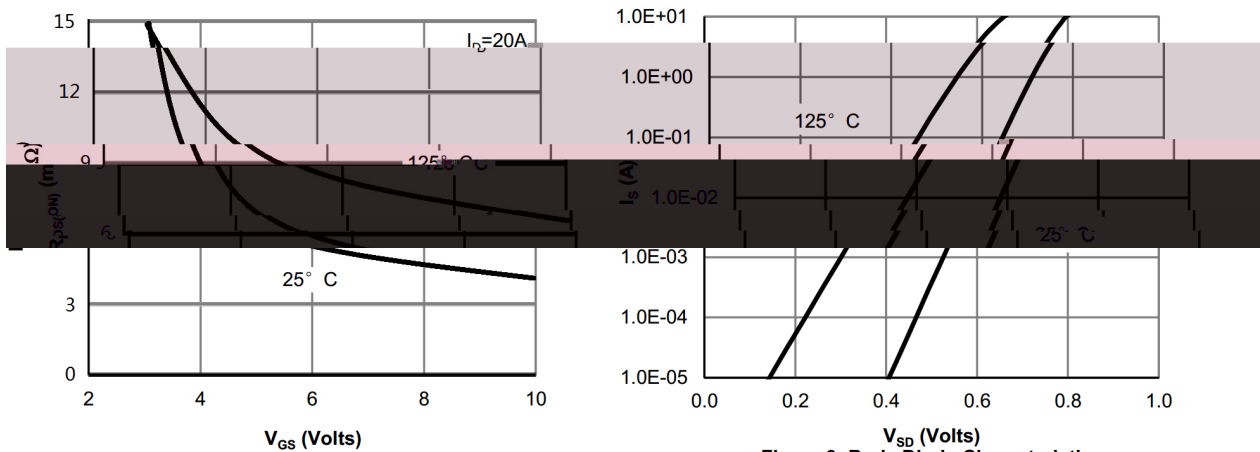
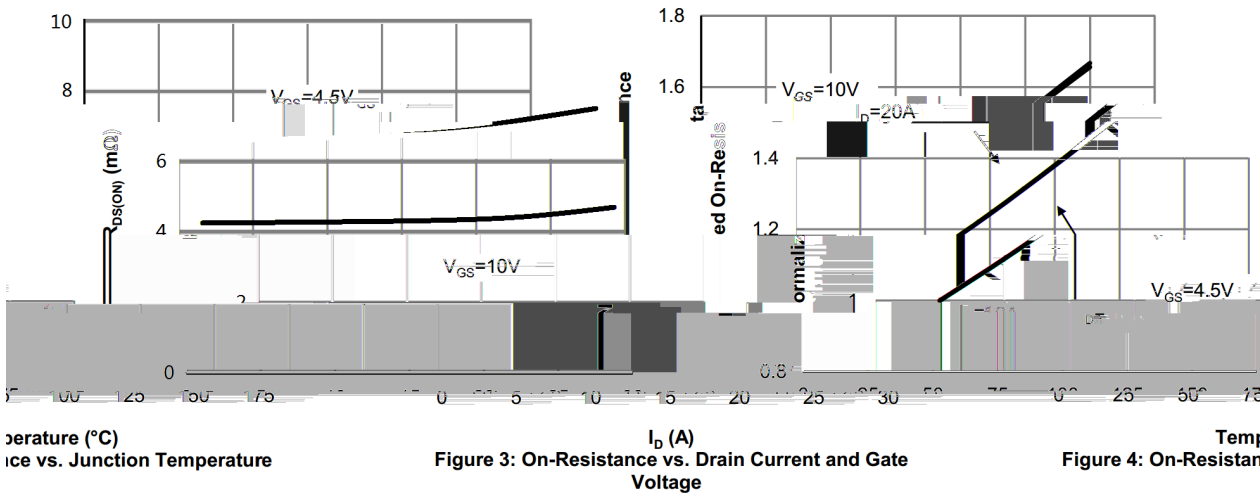
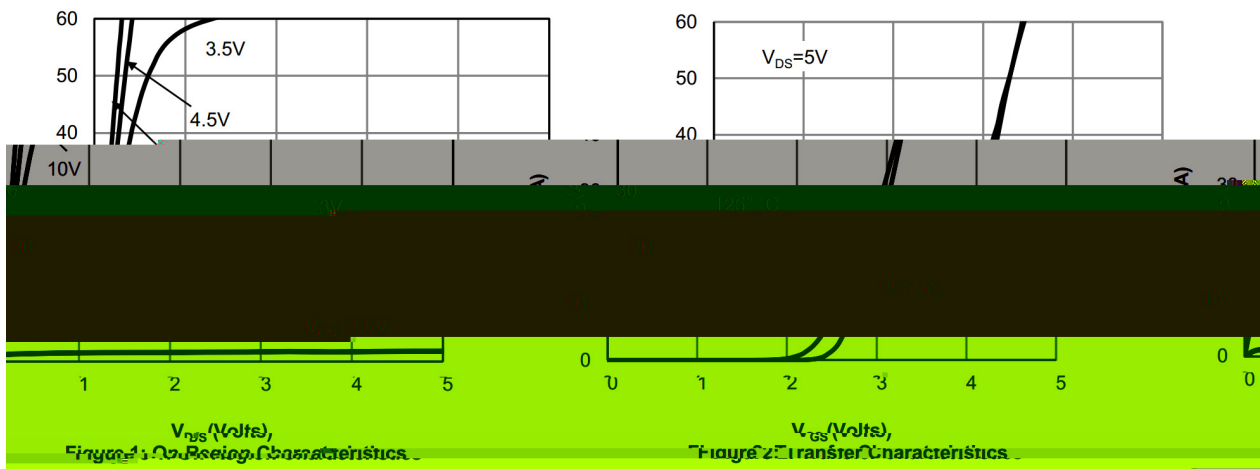
PIN1 G PIN 2 D PIN 3 S PIN 4 D

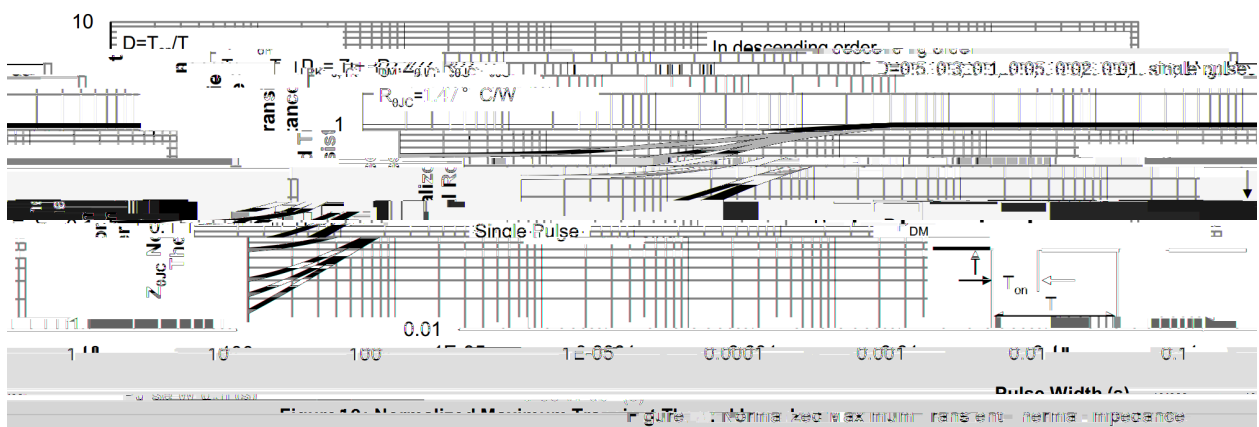
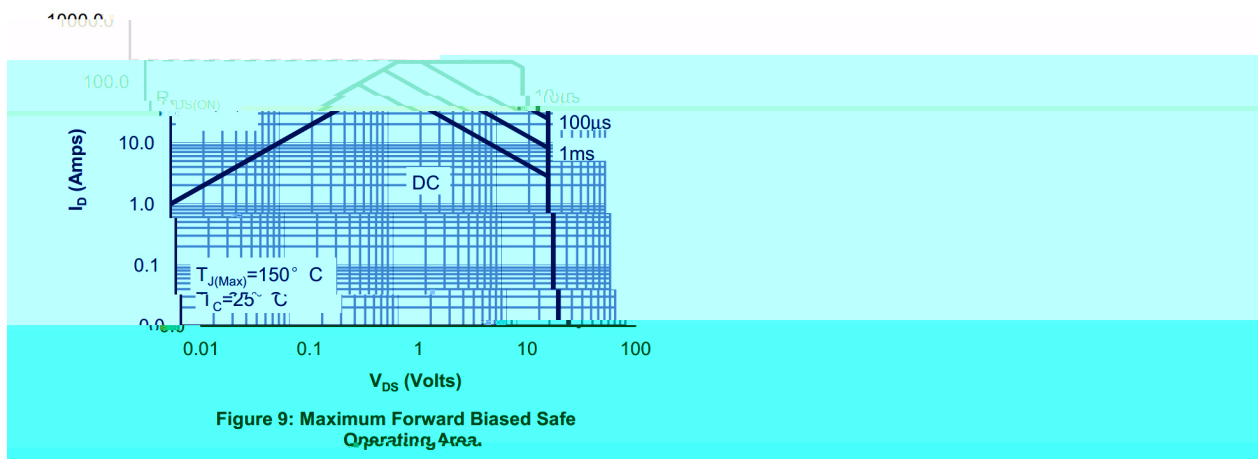
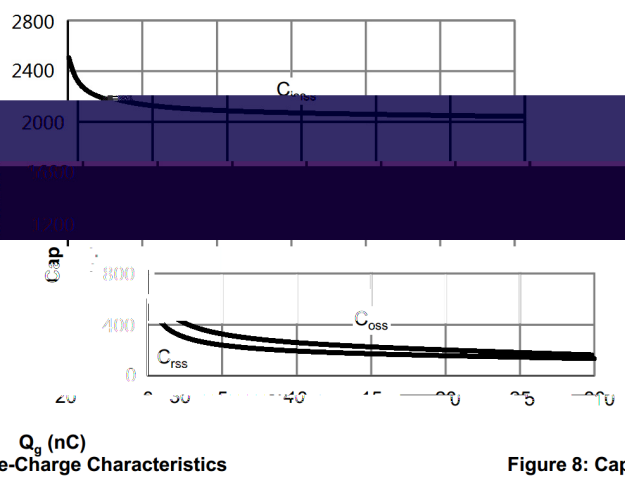
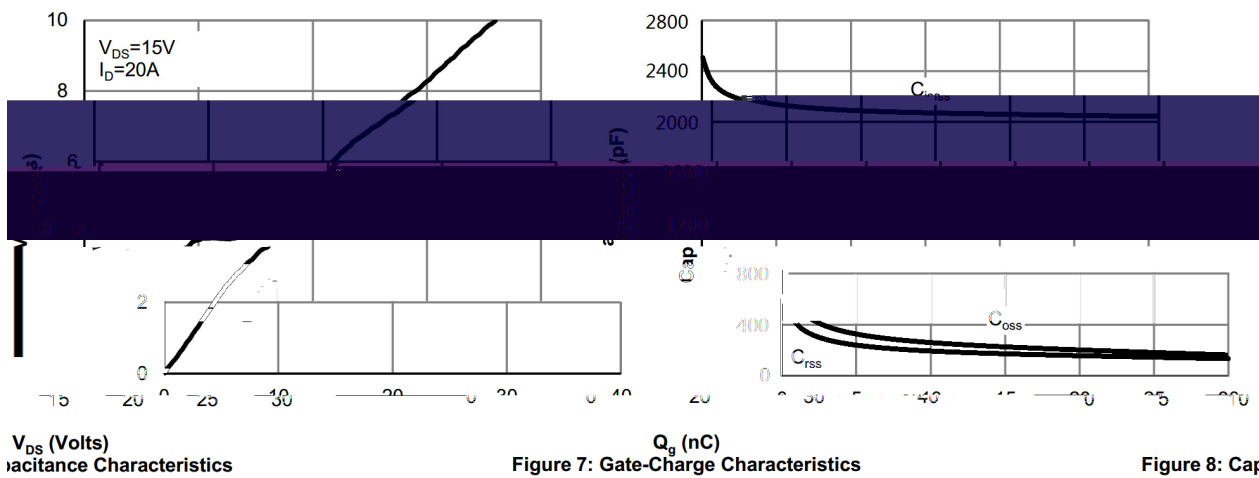
See Marking Instructions.

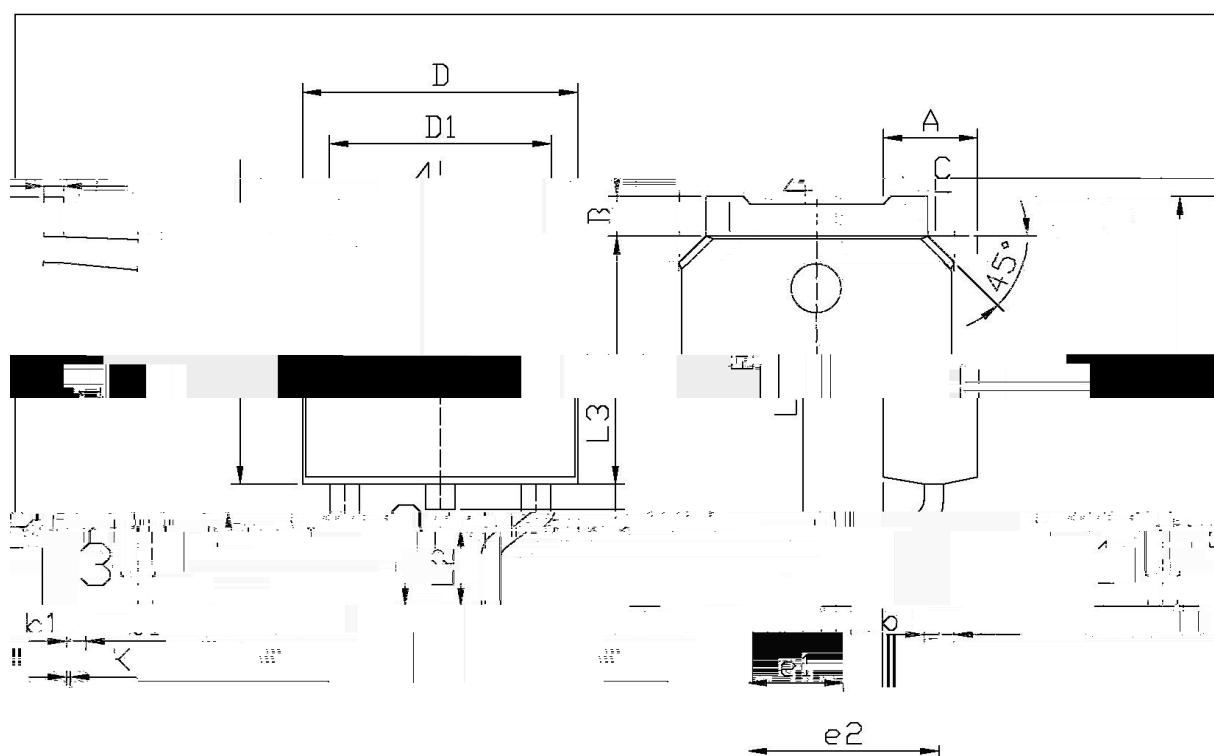
Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	30	V
Drain Current		$I_D(T_c=25^{\circ}\text{C})$	100	A
Drain Current - Pulsed		I_{DM}	215	A
Gate-Source Voltage		V_{GS}	± 20	V
Avalanche Current		I_{AS}	23.5	A
Single Pulsed Avalanche Energy(L=0.5mH)		E_{AS}	220.9	mJ
Power Dissipation		$P_D(T_c=25^{\circ}\text{C})$	85	W
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	$^{\circ}\text{C}$
Thermal Resistance-Junction to Ambient	$t \leq 10\text{s}$	$R_{\theta JA}$	20	$^{\circ}\text{C/W}$
	Steady-State		50	
Thermal Resistance-Junction to Case	Steady-State	$R_{\theta JC}$	1.47	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DS}	$V_{GS}=0\text{V}$ $I_D=250\mu\text{A}$	30			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=30\text{V}$ $V_{GS}=0\text{V}$			1.0	μA
Gate-Body Leakage Current Forward	I_{GSS}	$V_{GS}=\pm 20\text{V}$ $V_{DS}=0\text{V}$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250\mu\text{A}$	1.0	1.7	2.5	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10\text{V}$ $I_D=20\text{A}$		4.3	5	m Ω
		$V_{GS}=4.5\text{V}$ $I_D=10\text{A}$		6.7	8	
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0\text{V}$ $I_S=1\text{A}$		0.72	1.4	V
Gate resistance	R_g	$V_{GS}=0\text{V}$ $V_{DS}=0\text{V}$, $f=1\text{MHz}$		3.1		Ω
Input Capacitance	C_{iss}	$V_{DS}=25\text{V}$ $V_{GS}=0\text{V}$ $f=1.0\text{MHz}$		2030		pF
Output Capacitance	C_{oss}			168		
Reverse Transfer Capacitance	C_{rss}			163		
Total Gate Charge	$Q_{g(10V)}$	$V_{GS}=10\text{V}$, $V_{DS}=15\text{V}$, $I_D=20\text{A}$		40		nC
Total Gate Charge	$Q_{g(4.5V)}$			22		
Gate Source Charge	Q_{gs}			11		
Gate Drain Charge	Q_{gd}			5		

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=10V$ $V_{DS}=15V$ $R_L=0.75\ \Omega$ $R_{GEN}=3\ \Omega$		11		ns
Turn-On Rise Time	t_r			14		
Turn-Off Delay Time	$t_{d(off)}$			38		
Turn-Off Fall Time	t_f			10		





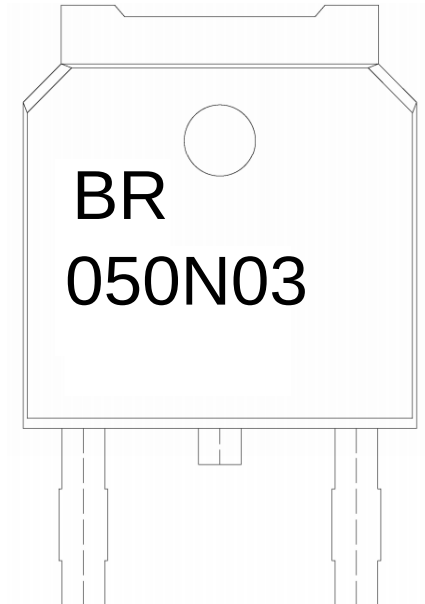


单位: mm

Symbol		Dimensions In Millimeters		Symbol		Dimensions In Millimeters	
		Min	Max			Min	Max
5	6.25			2.20	2.40		
2.24	2.34			B	0.95	1.25	e1
1.2	1.3			b	0.70	0.80	e2
9.85	10.35			b1	0.45	0.55	L1
L3	0.60	0.90		D1	6.45	6.75	
50	K	0.00	0.10				

□-252

T



BR

050N03

Note:

BR:

Company Code

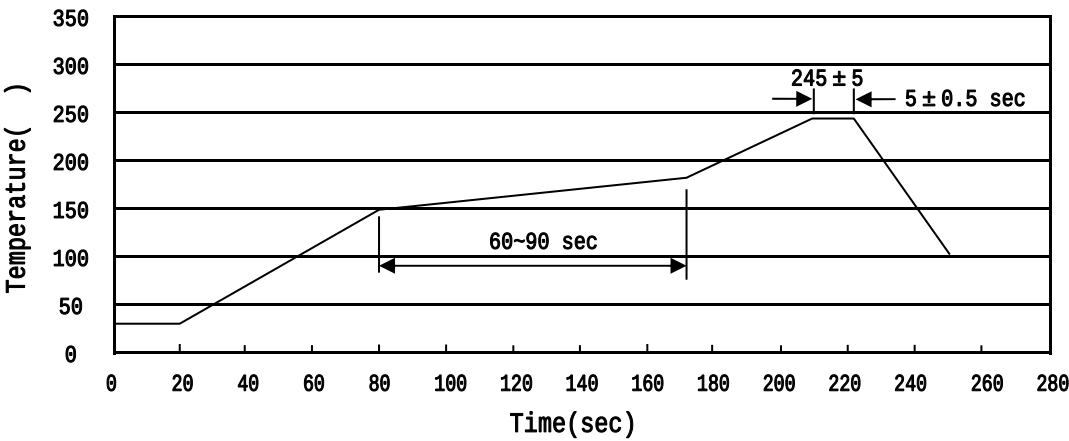
050N03:

Product Type Code

****:

Lot No. Code, code change with Lot No

Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

- 1

150 180

60 90sec;

1.Preheating:150~180 , Time:60~90sec.
- 2

245±5

5±0.5sec;

2.Peak Temp.:245±5 , Duration:5±0.5sec.
- 3

2 10 /sec.

3. Cooling Speed: 2~10 /sec.

260±5

10±1 sec.

Temp.:260±5℃

Time:10±1 sec

/ REEL

Package Type	Units					Dimension (unit mm ³)		
TO-252	2,500	2	5,000	6	30,000	13" ×16	360×360×50	380×335×366

/ TUBE

Package Type	Units					Dimension (unit mm ³)		
TO-251/252	75	48	3,600	5	18,000	526×20.5×5.25	555×164×50	575×290×180